

INFORMATION DISCLOSURE CITATION FORM FOR PATENT APPLICATION (FORM PTO-1449) (Substitute)			Docket No.: YOR920030207US1 Applicant(s): Hyungjun KIM et al. Filing Date:		Serial No.: Group:	
U.S. PATENTS						
Initials	Patent Number	Issue Date	Name	Class	Sub-class	Filing date
	2003/0201537A U.S. Patent Application Serial No. 10/699,226	10/30/03	Lane et al. KIM et al.			
FOREIGN PATENT DOCUMENTS						
Initials	Document Number	Date	Country	Name	Translation? Yes/No/n/a	
OTHER DOCUMENTS (Title, Author, Date, Pages, Etc., if known)						
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Examiner's Signature:				Date Considered:		
Initial if reference was considered, whether or not citation is in conformance with MPEP. Mark through citation if not considered. Include a copy of this citation form with your next correspondence to the Applicant(s).						